

N-Channel Enhancement Mode Power MOSFET

Description

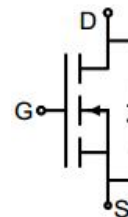
The G2014 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

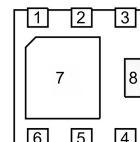
- V_{DS} 20V
- I_D (at $V_{GS} = 10V$) 14A
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 9m Ω
- $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) < 11m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

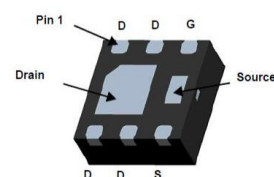
- Power switch
- DC/DC converters



Schematic diagram



pin assignment



DFN2x2-6L

Ordering Information

Device	Package	Marking	Packaging
G2014	DFN6L-2*2	G2014	3000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Continuous Drain Current	I_D	14	A
		8.9	
Pulsed Drain Current (note1)	I_{DM}	56	A
Gate-Source Voltage	V_{GS}	± 12	V
Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

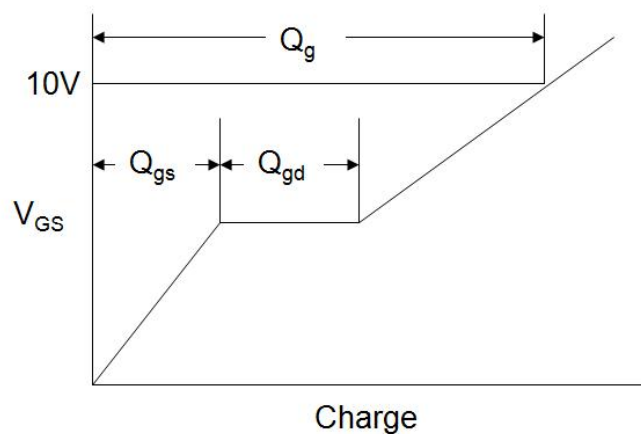
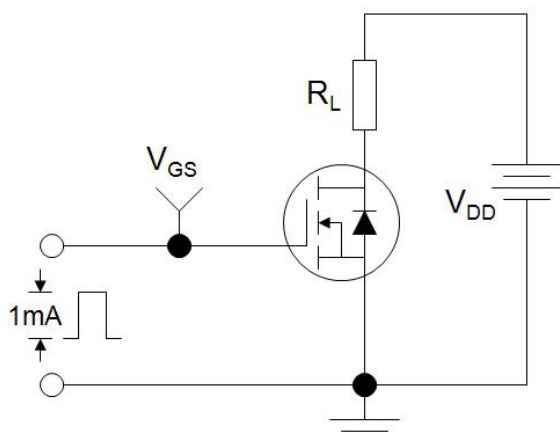
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient, $t \leq 10s$	R_{thJA}	41.7	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±12V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5	0.6	0.9	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 3A	--	7.2	9.0	mΩ
		V _{GS} = 2.5V, I _D = 2A	--	8.5	11	
Forward Transconductance	g _{FS}	V _{DS} = 5V, I _D = 3A	--	20	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1.0MHz	--	1600	--	pF
Output Capacitance	C _{oss}		--	270	--	
Reverse Transfer Capacitance	C _{rss}		--	250	--	
Total Gate Charge	Q _g	V _{DD} = 10V, I _D = 3A, V _{GS} = 4.5V	--	24	--	nC
Gate-Source Charge	Q _{gs}		--	2	--	
Gate-Drain Charge	Q _{gd}		--	5	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10V, I _D = 3A, R _G = 3Ω	--	11	--	ns
Turn-on Rise Time	t _r		--	20	--	
Turn-off Delay Time	t _{d(off)}		--	106	--	
Turn-off Fall Time	t _f		--	53	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	14	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 3A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = 3A, V _{GS} = 0V di/dt=100A/us	--	17	--	nC
Reverse Recovery Time	T _{rr}		--	36	--	ns

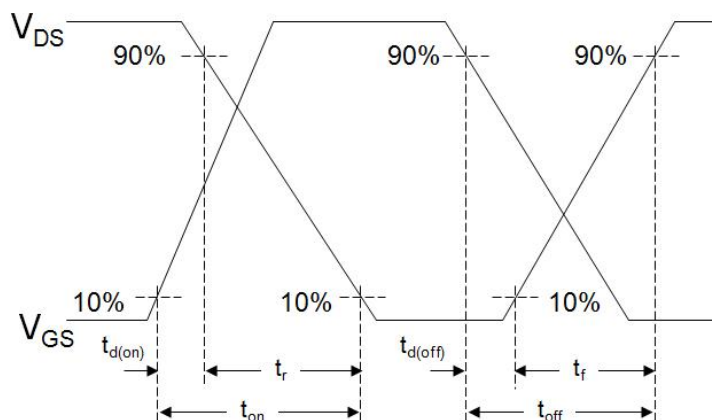
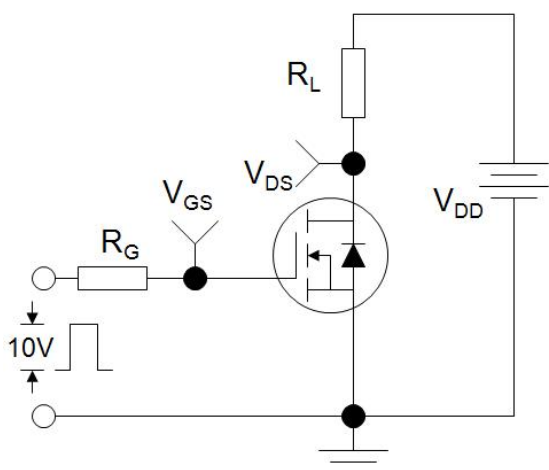
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

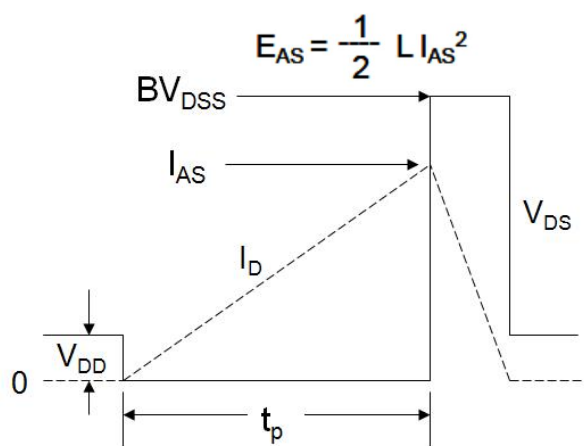
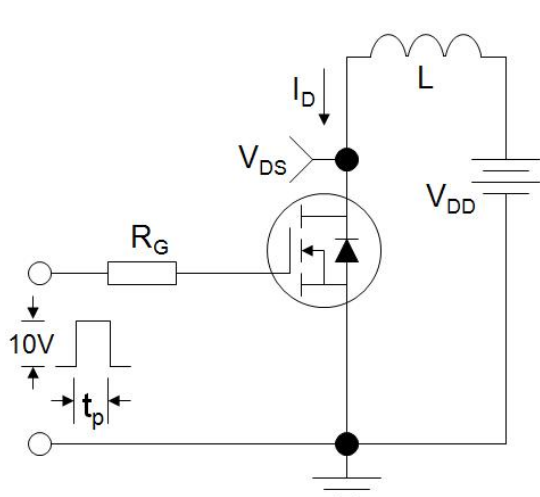
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

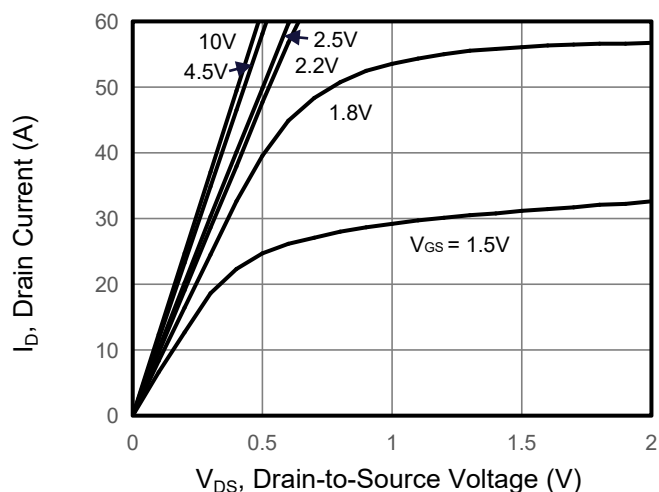


Figure 2. Transfer Characteristics

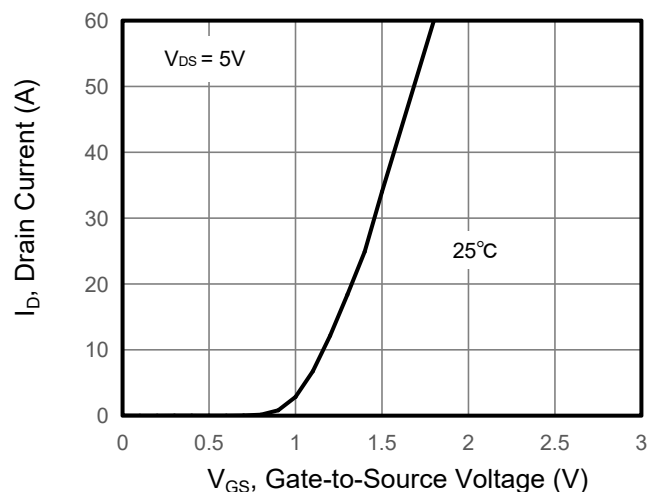


Figure 3. Drain Source On Resistance

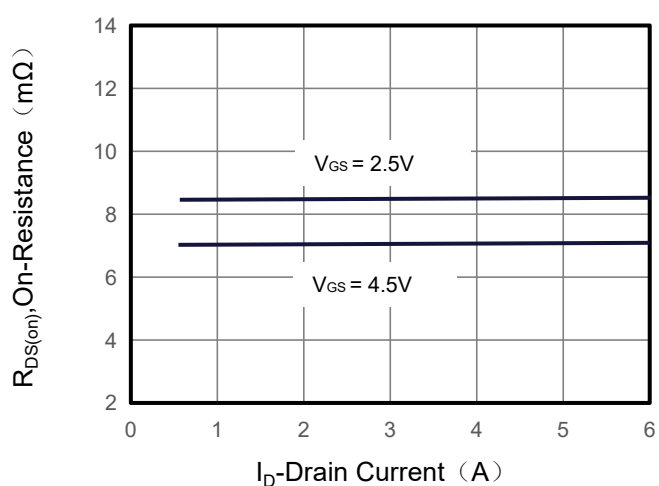


Figure 4. Gate Charge

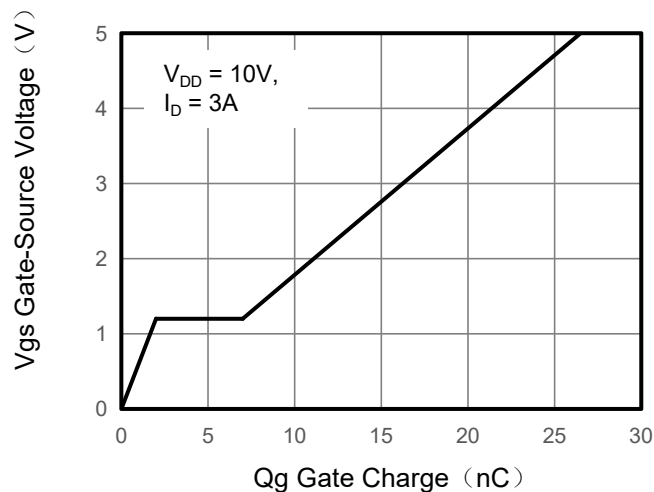


Figure 5. Capacitance

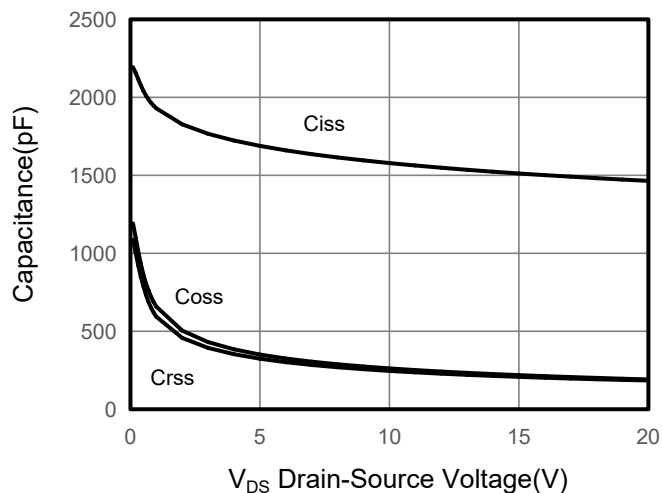
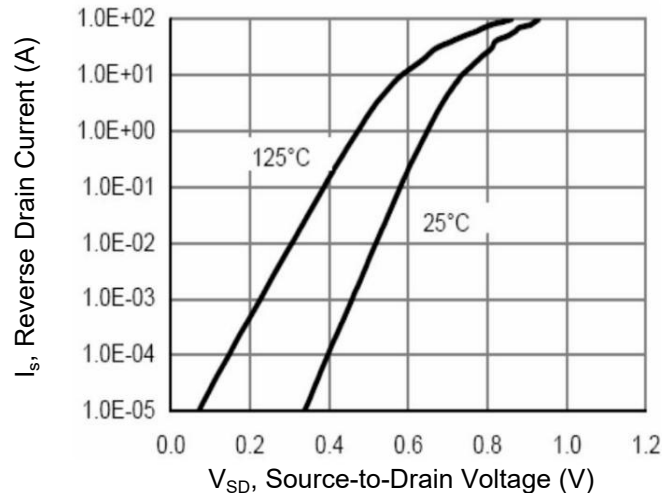


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

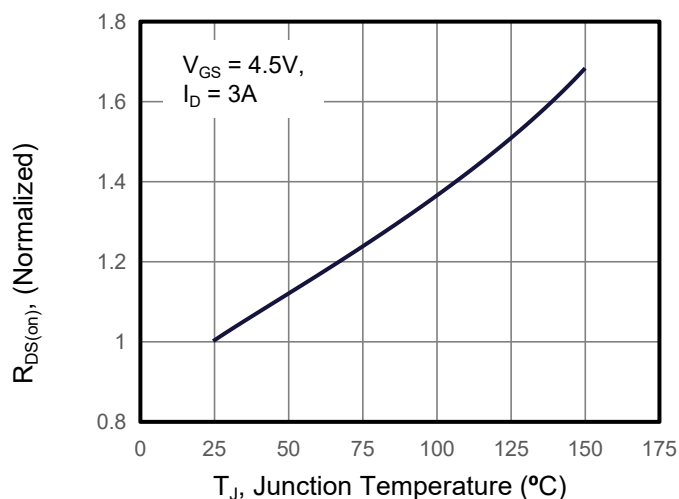


Figure 8. Safe Operation Area

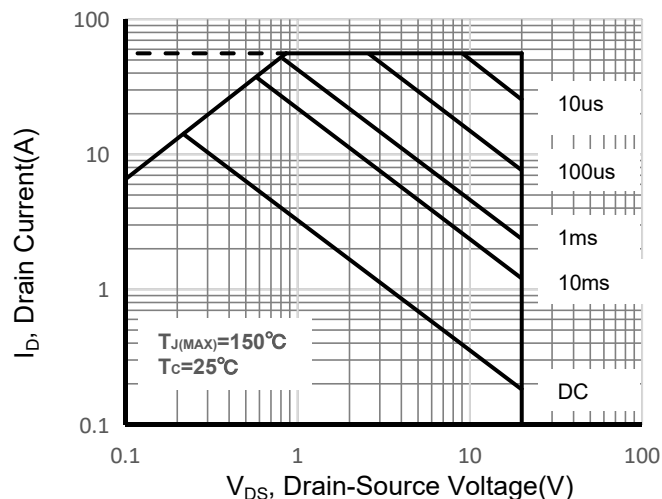


Figure 9. Maximum Continuous Drain Current vs Case Temperature

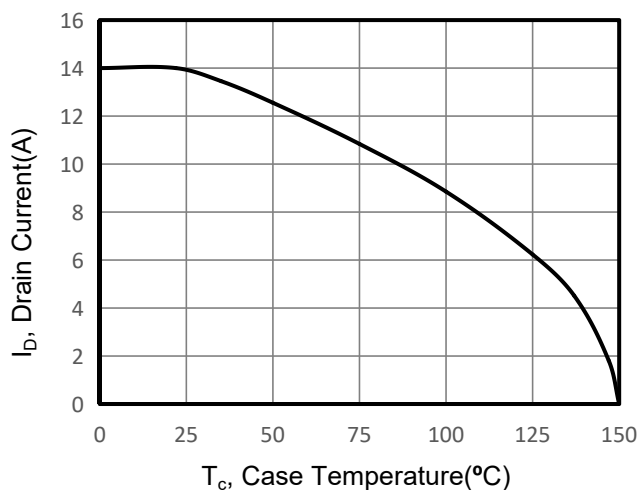
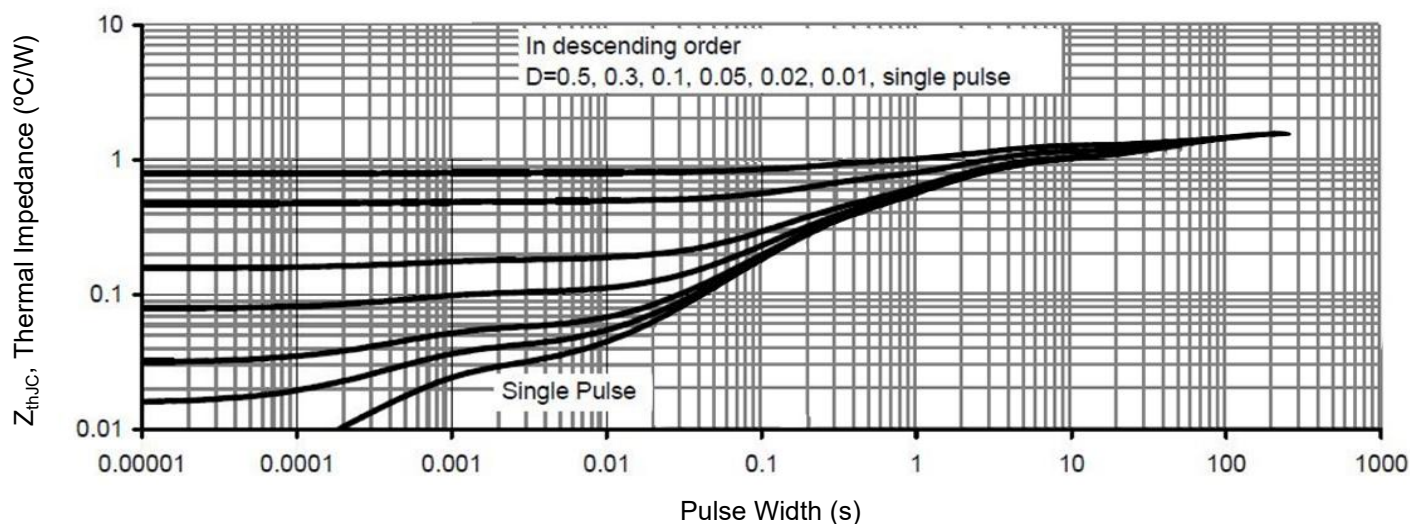
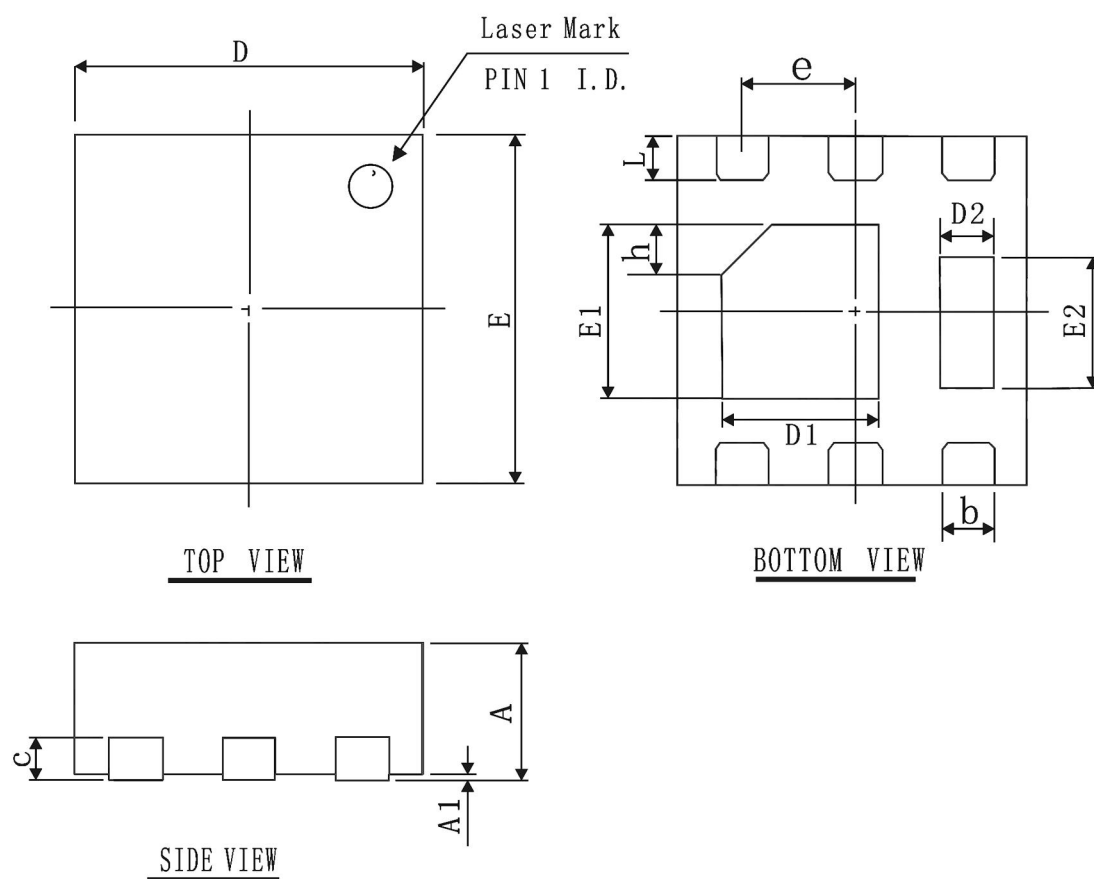


Figure 10. Normalized Maximum Transient Thermal Impedance



DFN6L-2*2 Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.20	0.25	0.30
D	1.95	2.00	2.07
E	1.95	2.00	2.07
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
c	0.203 REF		
e	0.65 BSC		